

**IN THE CLAIMS**

Please amend the following claims.

1-29 (cancelled)

30. (currently amended) A method of forming a semiconductor device comprising:

forming a gate electrode having a first thickness on a gate dielectric layer formed on a ~~first surface of a~~ substrate;

forming a pair of source/drain regions on opposite sides of the gate electrode;

forming a silicon germanium film having a second thickness on the gate electrode;

forming a silicon germanium film having the second thickness on the source/drain regions;

forming a silicide layer having a third thickness on the silicon germanium films; and

forming a pair of sidewall spacers having a ~~first~~ height above the ~~substrate surface on opposite sides of the gate electrode, wherein the first height is greater than the sum of the first, second and third thicknesses on the gate electrode~~ third thickness of the silicide layer on the silicon germanium film on the gate electrode.

31. (cancelled)

32. (currently amended) The method of claim 31 30, wherein the sidewall spacers comprise silicon nitride.

33. (cancelled)

34. (cancelled)

35. (cancelled)

36. (previously presented) The method of claim 30 wherein the gate electrode comprises polysilicon.

37. (previously presented) The method of claim 30 wherein the sidewall spacers are less than 300Å in width.